

MONOLITHIC DUAL H BRIDGE DRIVER CIRCUIT

DESCRIPTION

The μ PD16818 is a monolithic dual H bridge driver IC which uses N-channel power MOS FETs in its output stage. By employing the power MOS FETs for the output stage, this driver circuit has a substantially improved saturation voltage and power consumption as compared with conventional driver circuits that use bipolar transistors.

In addition, the drive current can be adjusted by an external resistor in power-saving mode.

The μ PD16818 is therefore ideal as the driver circuit of a 2-phase excitation, bipolar-driven stepping motor for the head actuator of an FDD.

FEATURES

- Compatible with 3V-/5V- supply voltage
- Pin compatible with μ PD16803
- Low ON resistance (sum of ON resistors of top and bottom MOS FETs)
 - $R_{ON1} = 1.2 \Omega$ ($V_M = 3.0$ V)
 - $R_{ON2} = 1.0 \Omega$ ($V_M = 5.0$ V)
- Low current consumption: $I_{DD} = 0.4$ mA TYP. ($V_{DD} = 2.7$ V to 3.6 V)
- Stop mode function that turns OFF all output MOS FETs
- Drive current can be set in power-saving mode (set by external resistor)
- Compact surface mount package

ORDERING INFORMATION

Part Number	Package
μ PD16818GS	20-pin plastic SOP (300 mil)
μ PD16818GR-8JG	20-pin plastic SSOP (225 mil)

ABSOLUTE MAXIMUM RATINGS ($T_A = 25$ °C)

Parameter		Symbol	Condition	Rating	Unit
Supply voltage	Motor block	V_M		-0.5 to +7.0	V
	Control block	V_{DD}		-0.5 to +7.0	
Power consumption	μ PD16818GS	P_{D1}		1.0 ^{Note 1}	W
		P_{D2}		1.25 ^{Note 2}	
	μ PD16818GR-8JG	P_{D2S}		0.79 ^{Note 2}	
Instantaneous H bridge drive current		I_D (pulse)	$PW \leq 5$ ms, Duty ≤ 40 %	± 1.0 ^{Note 2}	A
Input voltage		V_{IN}		-0.5 to $V_{DD} + 0.5$	V
Operating temperature range		T_A		0 to 60	°C
Operation junction temperature		T_J (MAX)		150	°C
Storage temperature range		T_{stg}		-55 to +150	°C

Notes 1. IC only

2. When mounted on a glass epoxy printed circuit board (100 mm \times 100 mm \times 1 mm)

The information in this document is subject to change without notice.

RECOMMENDED OPERAING CONDITIONS

Parameter		Symbol	MIN.	TYP.	MAX.	Unit
Supply voltage	Motor block	V _M	2.7		6.0	V
	Control block	V _{DD}	2.7		6.0	
Rx pin connection resistance		R _X	2			kΩ
H bridge drive current (V _{DD} = V _M = 3 V) ^{Note}	μPD16818GS	I _{DR}			430	mA
	μPD16818GR-8JG	I _{DRS}			340	
Charge pump capacitor capacitance		C ₁ -C ₃	5		20	nF
Operating temperature		T _A	0		60	°C

Note When mounted on a glass epoxy printed circuit board (100 mm × 100 mm × 1 mm)

ELECTRICAL SPECIFICATIONS (Within recommended operating conditions unless otherwise specified)

V_{DD} = V_M = 4.0 V to 6.0 V

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
OFF V _M pin current	I _M	INC pin low V _M = V _{DD} = 6 V			1.0	μA
V _{DD} pin current	I _{DD}	Note 1		1.0	2.0	mA
High-level input current (IN ₁ , IN ₂ , INC)	I _{IH1}	T _A = 25 °C, V _{IN} = V _{DD}			1.0	μA
		0 ≤ T _A ≤ 60 °C, V _{IN} = V _{DD}			2.0	
Low-level input current (IN ₁ , IN ₂ , INC)	I _{IL1}	T _A = 25 °C, V _{IN} = 0			-0.15	mA
		0 ≤ T _A ≤ 60 °C, V _{IN} = 0			-0.2	
PS pin high-level input current	I _{IH2}	T _A = 25 °C, V _{IN} = V _{DD}			0.15	mA
		0 ≤ T _A ≤ 60 °C, V _{IN} = V _{DD}			0.2	
PS pin low-level input voltage	I _{IL2}	T _A = 25 °C, V _{IN} = 0			-1.0	μA
		0 ≤ T _A ≤ 60 °C, V _{IN} = 0			-2.0	
Input pull-up resistance (IN ₁ , IN ₂ , INC)	R _{INU}	T _A = 25 °C	35	50	65	kΩ
		0 ≤ T _A ≤ 60 °C	25		75	
PS pin input pull-down resistance	R _{IND}	T _A = 25 °C	35	50	65	kΩ
		0 ≤ T _A ≤ 60 °C	25		75	
Control pin high-level input voltage	V _{IH}		3.0		V _{DD} + 0.3	V
Control pin low-level input voltage	V _{IL}		-0.3		0.8	V
H bridge ON resistance ^{Note 2}	R _{ON2}	V _{DD} = V _M = 5 V		1.0	2.0	Ω
R _{ON} relative accuracy	ΔR _{ON}	Excitation direction <1>, <3>			±15	%
		Excitation direction <2>, <4> ^{Note 3}			±5	
Charge pump circuit turn ON time	t _{ONG}	V _{DD} = V _M = 5 V		0.3	2.0	ms
H bridge turn ON time	t _{ONH}	C ₁ = C ₂ = C ₃ = 10nF R _M = 20 Ω			2.0	μs
H bridge turn OFF time	t _{OFFH}				5.0	μs

- Notes 1.** When IN₁ = IN₂ = INC = "H", PS = "L"
- Sum of ON resistances of top and bottom MOS FETs
 - For the excitation direction, refer to **FUNCTION TABLE**.

ELECTRICAL SPECIFICATIONS (Within recommended operating conditions unless otherwise specified)

V_{DD} = V_M = 2.7 V to 3.6 V

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
OFF V _M pin current	I _M	INC pin low V _M = V _{DD} = 3.6 V			1.0	μA
V _{DD} pin current	I _{DD}	Note 1		0.4	1.0	mA
High-level input current (IN ₁ , IN ₂ , INC)	I _{IH1}	T _A = 25 °C, V _{IN} = V _{DD}			1.0	μA
		0 ≤ T _A ≤ 60 °C, V _{IN} = V _{DD}			2.0	
Low-level input current (IN ₁ , IN ₂ , INC)	I _{IL1}	T _A = 25 °C, V _{IN} = 0			-0.09	mA
		0 ≤ T _A ≤ 60 °C, V _{IN} = 0			-0.12	
PS pin high-level input current	I _{IH2}	T _A = 25 °C, V _{IN} = V _{DD}			0.09	mA
		0 ≤ T _A ≤ 60 °C, V _{IN} = V _{DD}			0.12	
PS pin low-level input voltage	I _{IL2}	T _A = 25 °C, V _{IN} = 0			-1.0	μA
		0 ≤ T _A ≤ 60 °C, V _{IN} = 0			-2.0	
Input pull-up resistance (IN ₁ , IN ₂ , INC)	R _{INU}	T _A = 25 °C	35	50	65	kΩ
		0 ≤ T _A ≤ 60 °C	25		75	
PS pin input pull-down resistance	R _{IND}	T _A = 25 °C	35	50	65	kΩ
		0 ≤ T _A ≤ 60 °C	25		75	
Control pin high-level input voltage	V _{IH}		2.0		V _{DD} + 0.3	V
Control pin low-level input voltage	V _{IL}		-0.3		0.8	V
H bridge ON resistance ^{Note 2}	R _{ON1}	V _{DD} = V _M = 3 V		1.2	2.4	Ω
R _{ON} relative accuracy	ΔR _{ON}	Excitation direction <1>, <3>			±15	%
		Excitation direction <2>, <4> ^{Note 3}			±5	
V _x voltage in power-saving mode ^{Note 4}	V _x	V _{DD} = V _M = 3 V R _x = 270 kΩ	1.0	1.2	1.4	V
V _x relative accuracy in power-saving mode	ΔV _x	Excitation direction <1>, <3>			±5	%
		Excitation direction <2>, <4>			±5	
Charge pump circuit turn ON time	t _{ONG}	V _{DD} = V _M = 3 V		0.3	2.0	ms
H bridge turn ON time	t _{ONH}	C ₁ = C ₂ = C ₃ = 10nF			2.0	μs
H bridge turn OFF time	t _{OFFH}	R _M = 20 Ω			5.0	μs

Notes 1. When IN₁ = IN₂ = INC = "H", PS = "L"

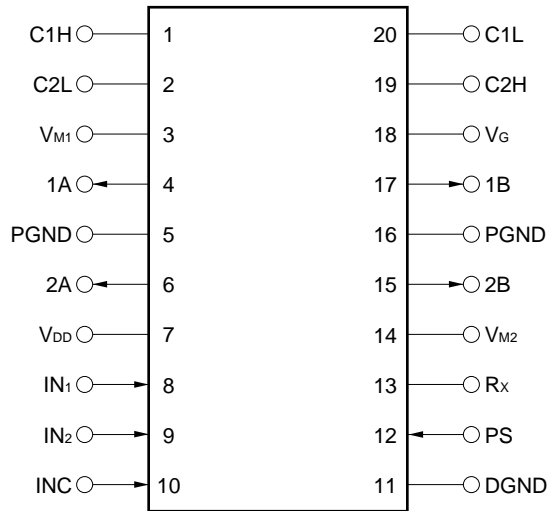
2. Sum of ON resistances of top and bottom MOS FETs

3. For the excitation direction, refer to **FUNCTION TABLE**.

4. V_x is a voltage at point A (FORWARD) or B (REVERSE) of the H bridge in **FUNCTION TABLE**.

PIN CONFIGURATION (Top View)

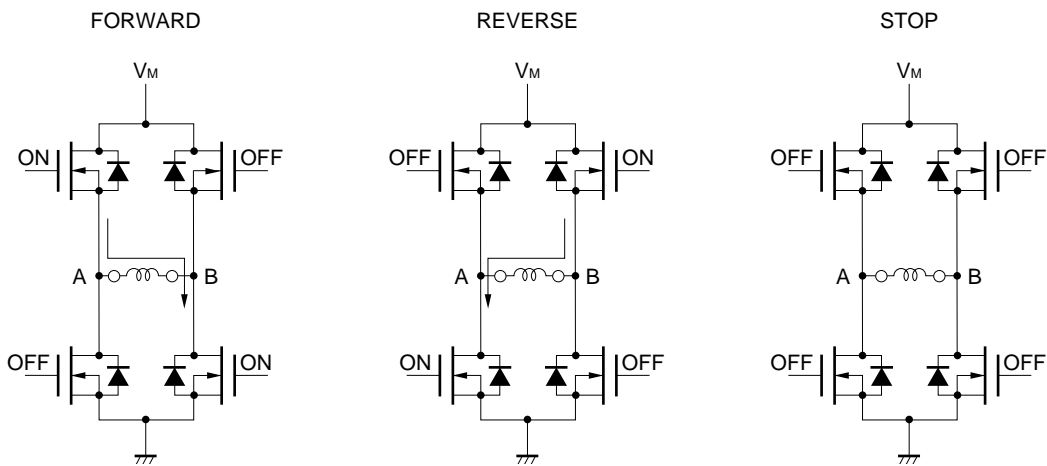
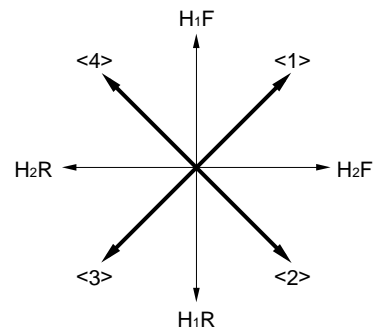
20-pin plastic SOP (300 mil)
20-pin plastic SSOP (225 mil)



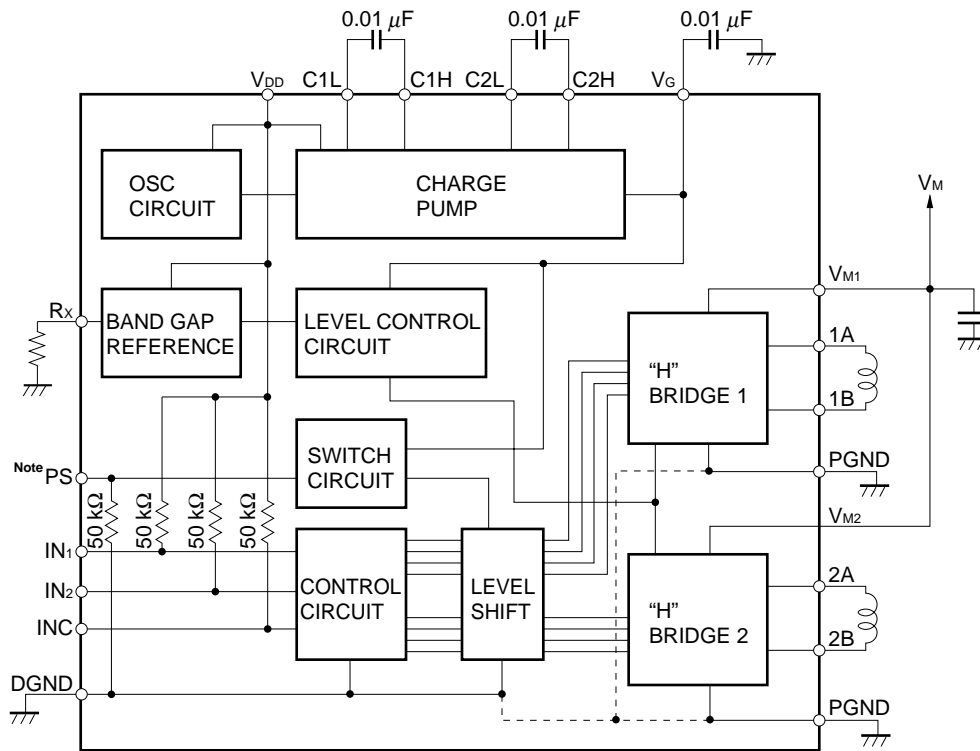
FUNCTION TABLE

Excitation Direction	INc	IN1	IN2	H1	H2
<1>	H	H	H	F	F
<2>	H	L	H	R	F
<3>	H	L	L	F	R
<4>	H	H	L	R	R
-	L	x	x	Stop	

F: FORWARD
R: REVERSE



BLOCK DIAGRAM

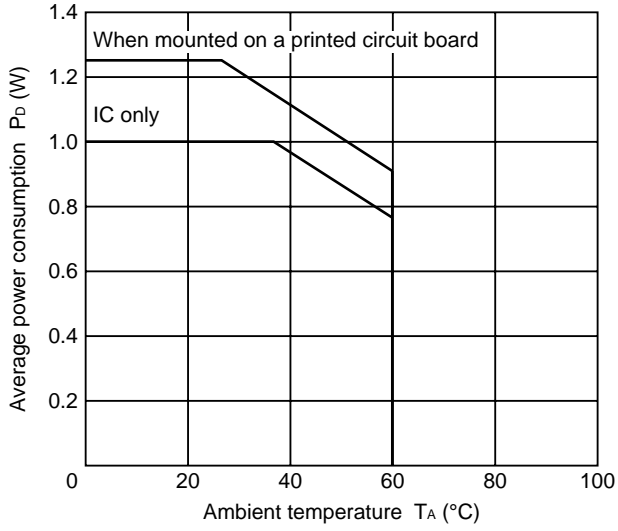


Note The power-saving mode is set when the PS pin goes high. In this mode, the voltage of the charge pump circuit is lowered and the ON resistance of the H bridge driver transistor increases, limiting the current.

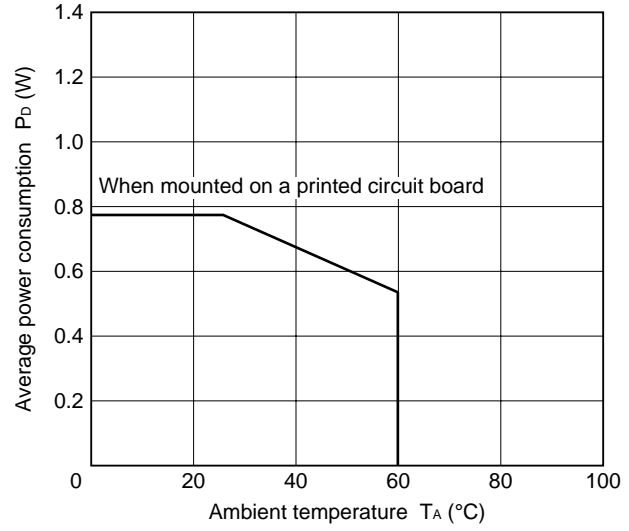
Remark ----- is connected in diffusion layer.

CHARACTERISTIC CURVES

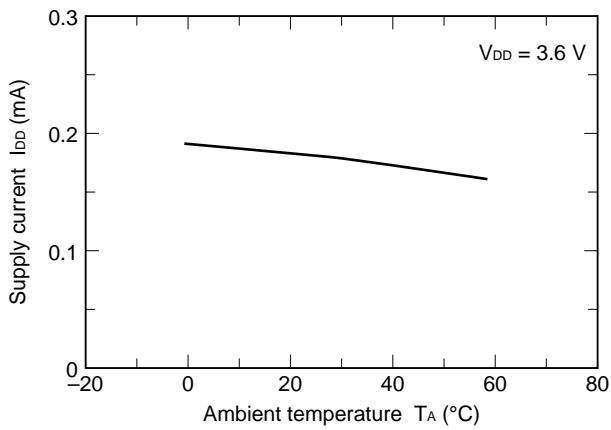
P_D vs. T_A Characteristics (μ PD16818GS)



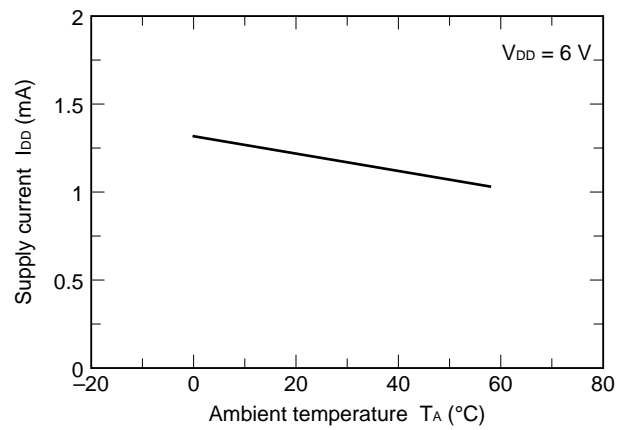
P_D vs. T_A Characteristics (μ PD16818GR-8JG)

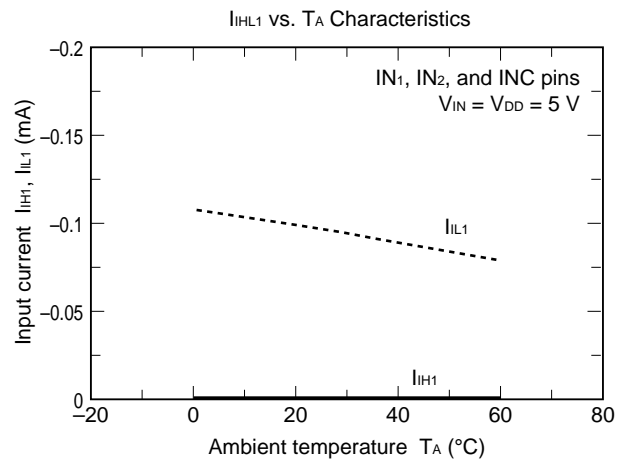
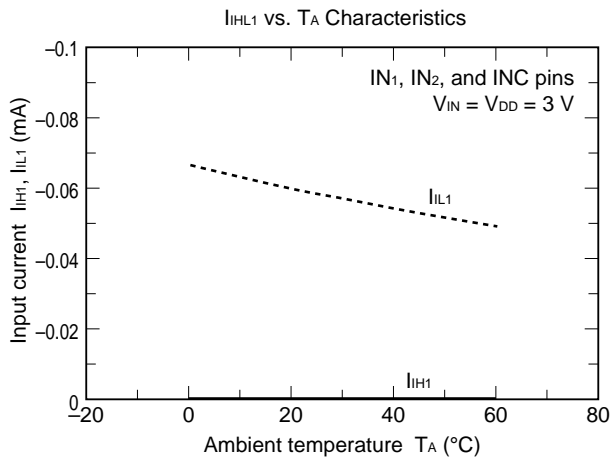
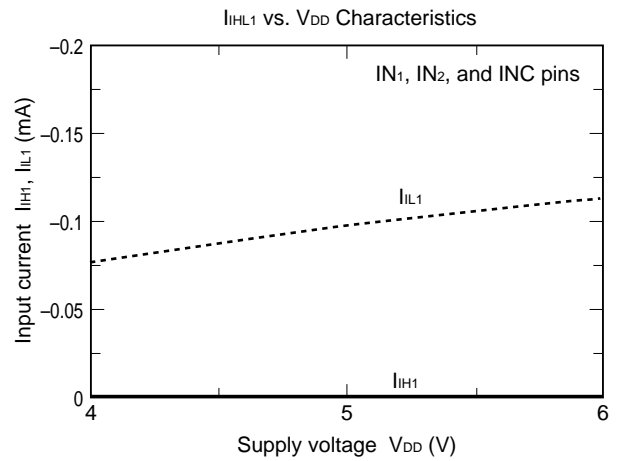
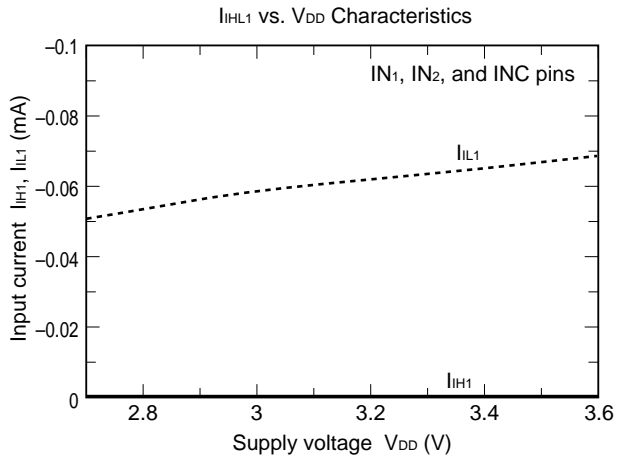


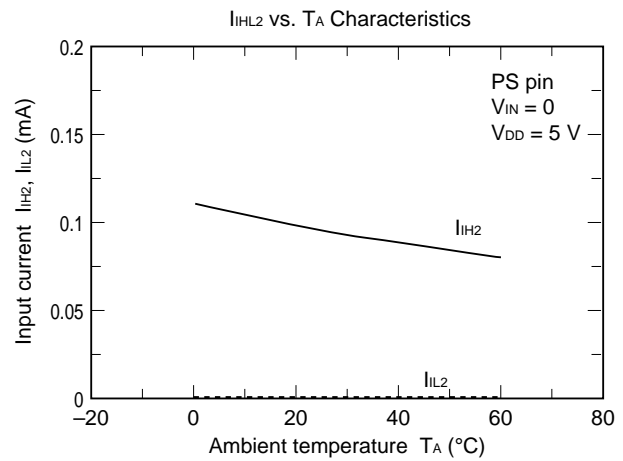
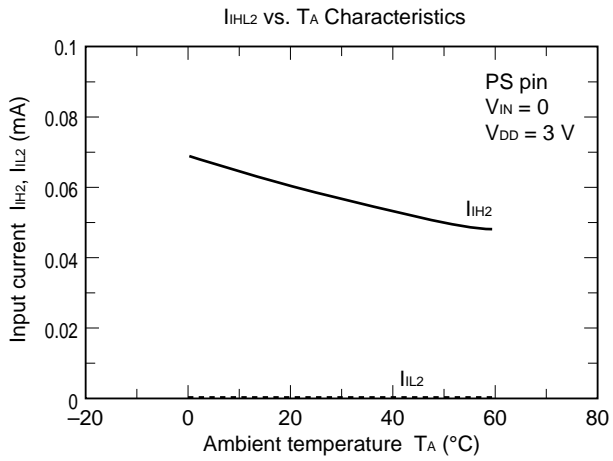
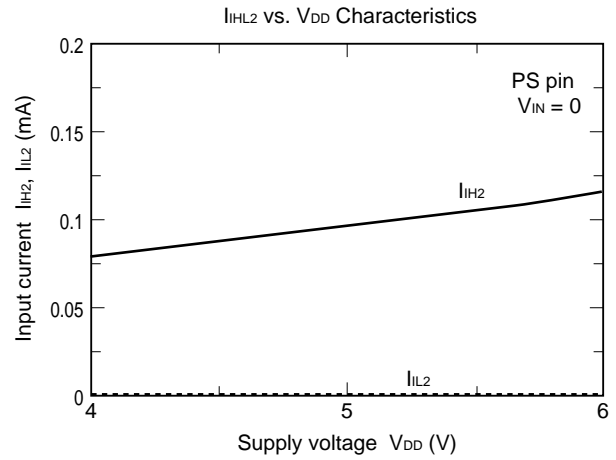
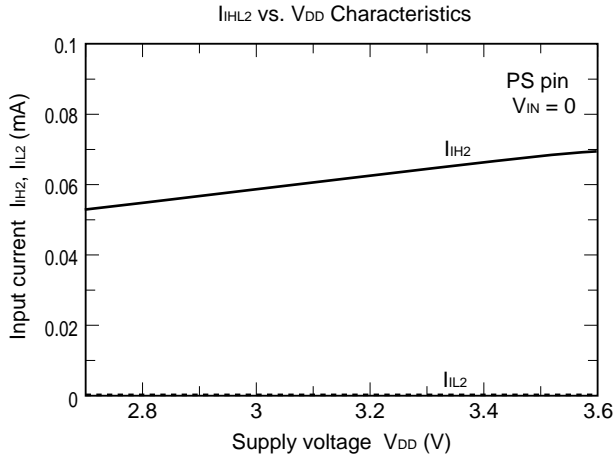
I_{DD} vs. T_A Characteristics

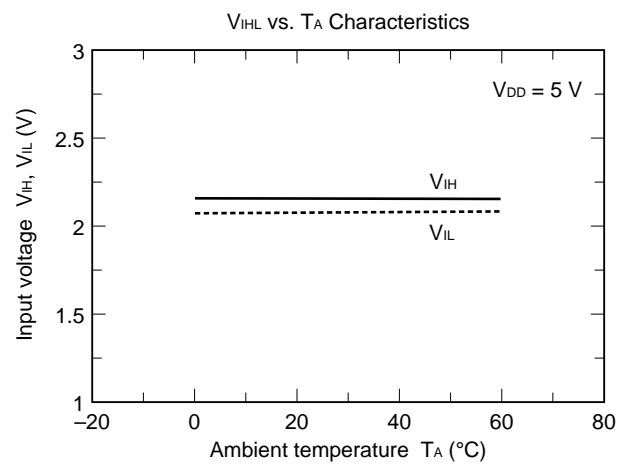
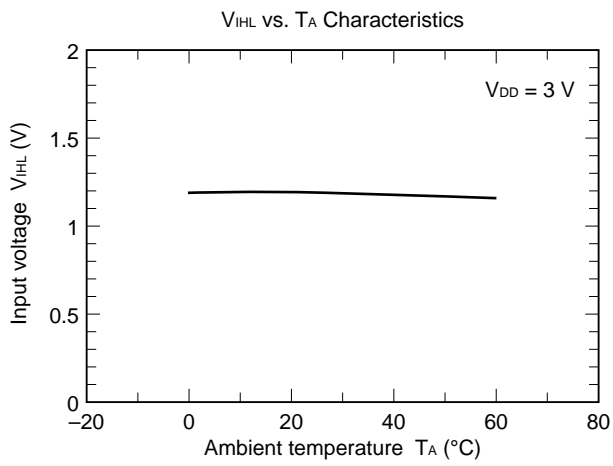
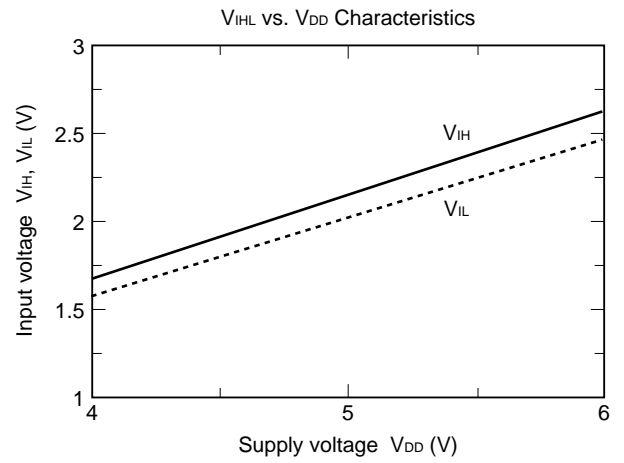
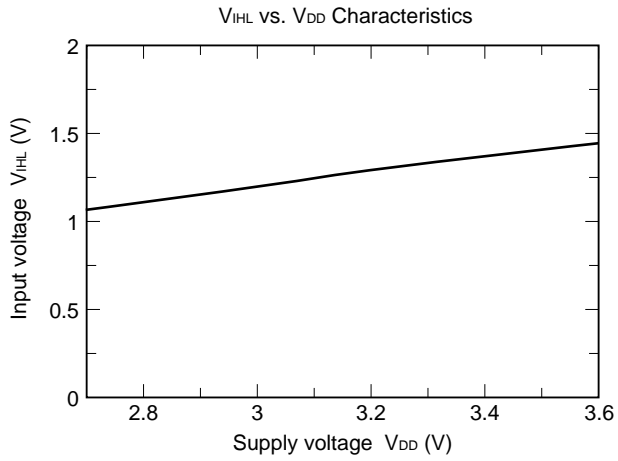


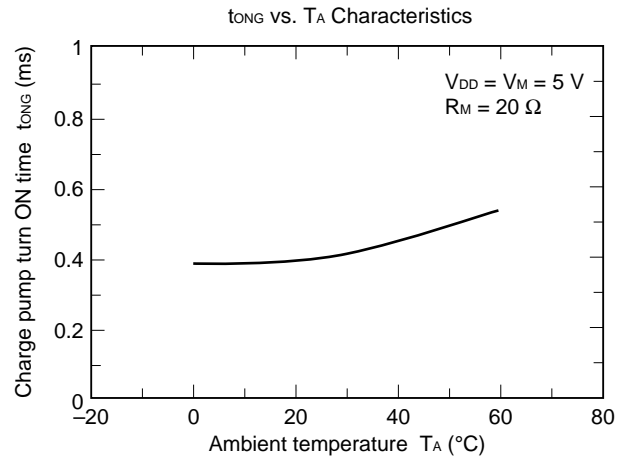
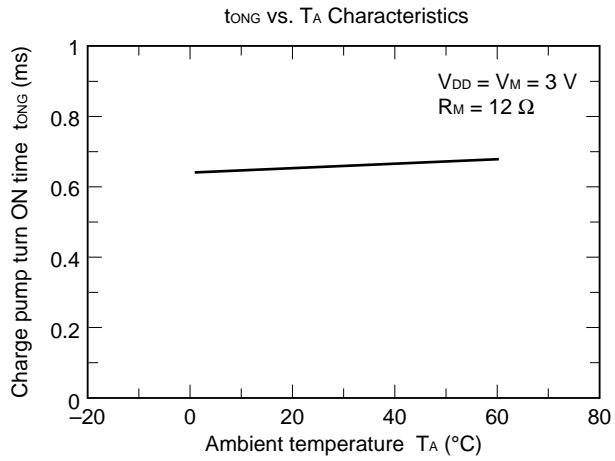
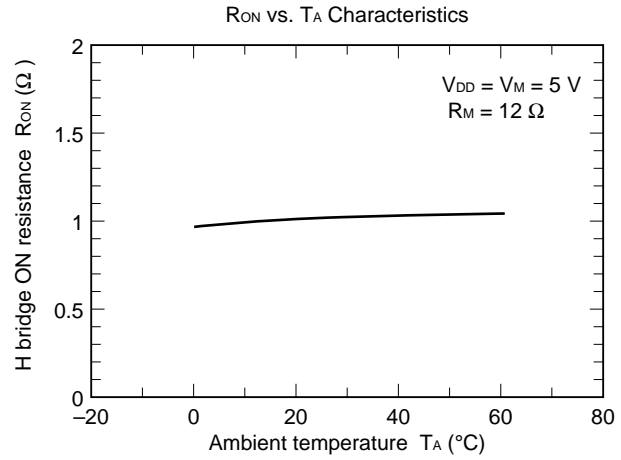
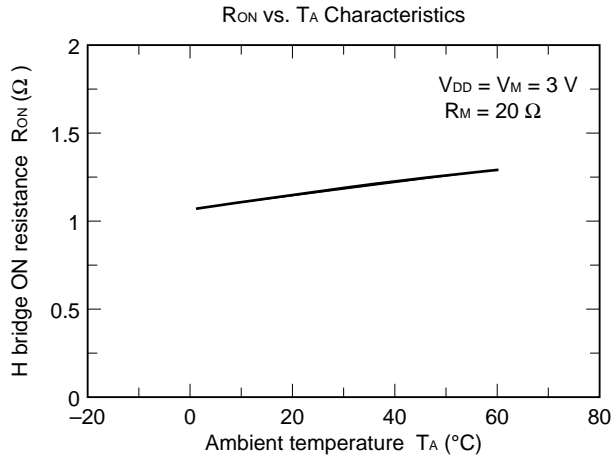
I_{DD} vs. T_A Characteristics

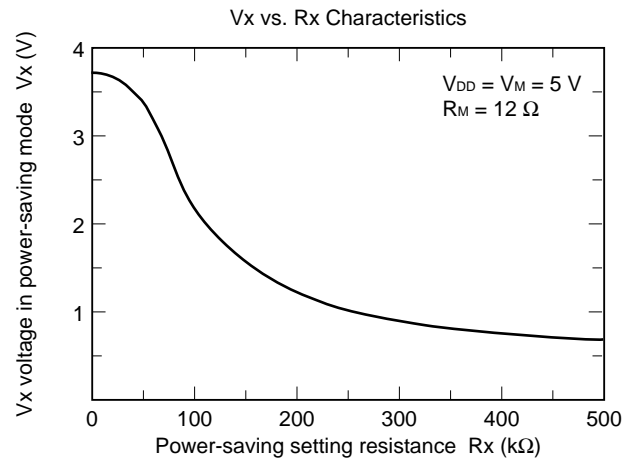
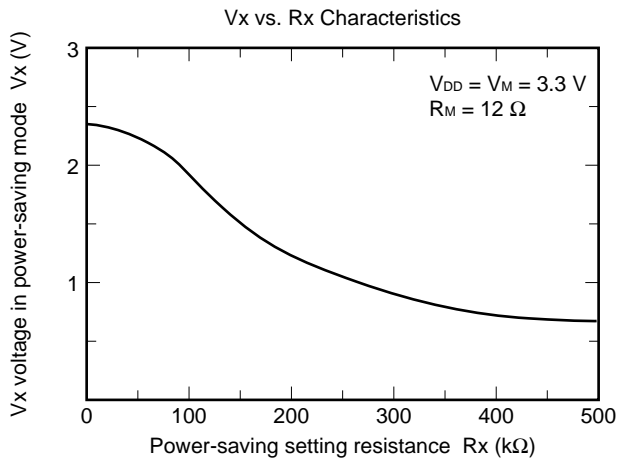
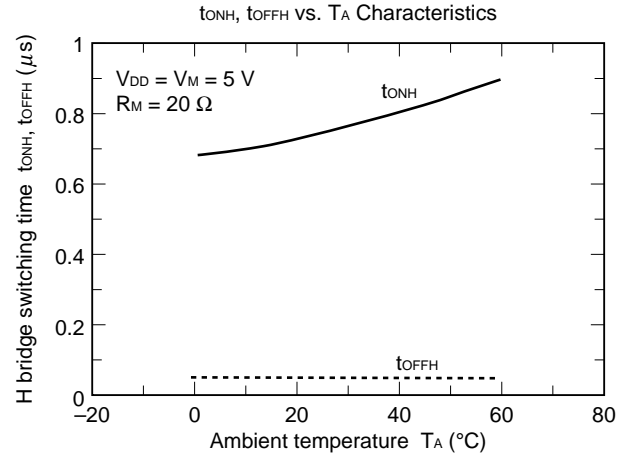
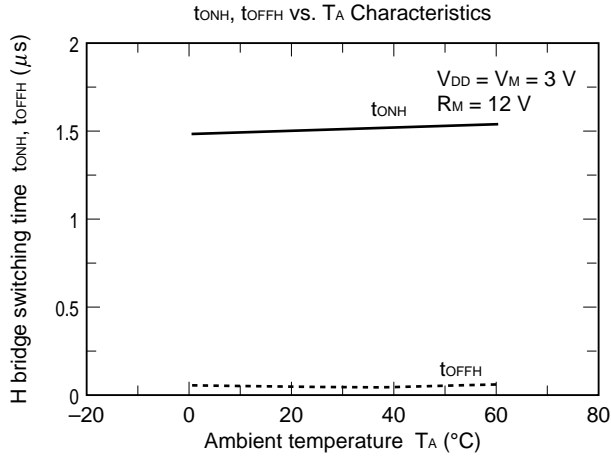






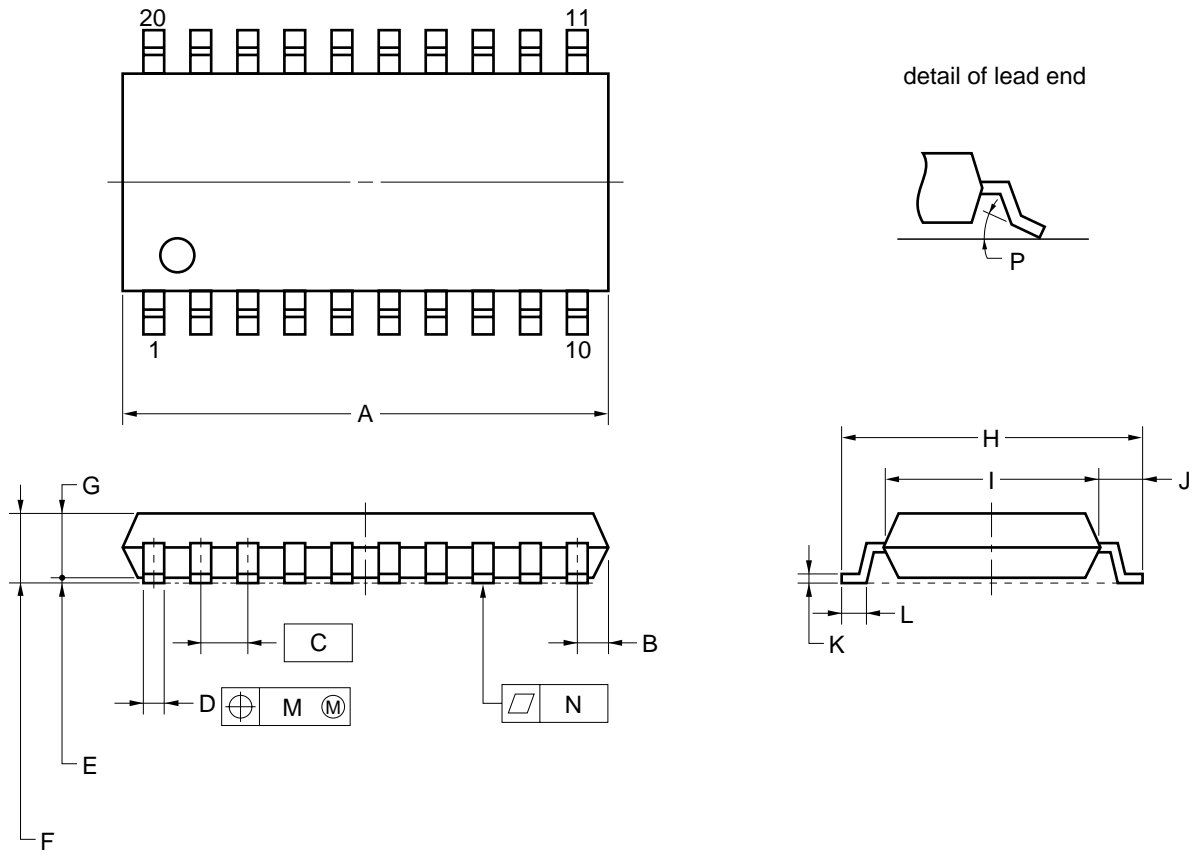






PACKAGE DRAWINGS

20 PIN PLASTIC SOP (300 mil)



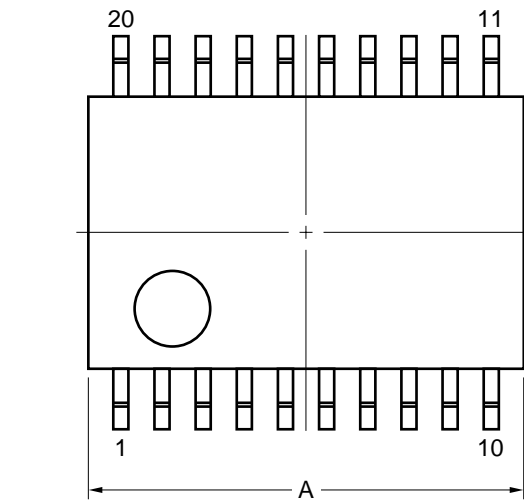
NOTE

Each lead centerline is located within 0.12 mm (0.005 inch) of its true position (T.P.) at maximum material condition.

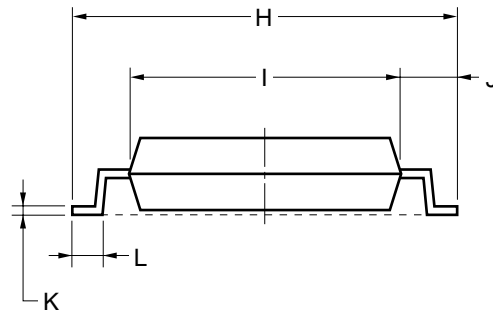
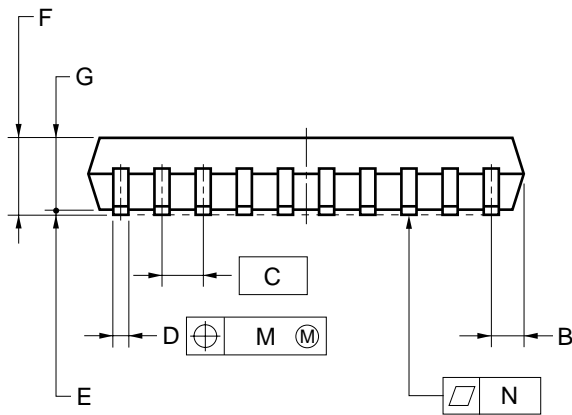
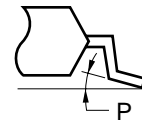
ITEM	MILLIMETERS	INCHES
A	12.7±0.3	0.500±0.012
B	0.78 MAX.	0.031 MAX.
C	1.27 (T.P.)	0.050 (T.P.)
D	0.42 ^{+0.08} _{-0.07}	0.017 ^{+0.003} _{-0.004}
E	0.1±0.1	0.004±0.004
F	1.8 MAX.	0.071 MAX.
G	1.55±0.05	0.061±0.002
H	7.7±0.3	0.303±0.012
I	5.6±0.2	0.220 ^{+0.009} _{-0.008}
J	1.1	0.043
K	0.22 ^{+0.08} _{-0.07}	0.009 ^{+0.003} _{-0.004}
L	0.6±0.2	0.024 ^{+0.008} _{-0.009}
M	0.12	0.005
N	0.10	0.004
P	3° ^{+7°} _{-3°}	3° ^{+7°} _{-3°}

P20GM-50-300B, C-5

20 PIN PLASTIC SHRINK SOP (225mil)



detail of lead end



NOTE

Each lead centerline is located within 0.10 mm (0.004 inch) of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS	INCHES
A	6.7±0.3	0.264 ^{+0.012} _{-0.013}
B	0.575 MAX.	0.023 MAX.
C	0.65 (T.P.)	0.026 (T.P.)
D	0.22 ^{+0.10} _{-0.05}	0.009 ^{+0.004} _{-0.003}
E	0.1±0.1	0.004±0.004
F	1.45 MAX.	0.057 MAX.
G	1.15±0.1	0.045 ^{+0.005} _{-0.004}
H	6.4±0.2	0.252±0.008
I	4.4±0.1	0.173 ^{+0.005} _{-0.004}
J	1.0±0.2	0.039 ^{+0.009} _{-0.008}
K	0.15 ^{+0.10} _{-0.05}	0.006 ^{+0.004} _{-0.002}
L	0.5±0.2	0.020 ^{+0.008} _{-0.009}
M	0.10	0.004
N	0.10	0.004
P	3° ^{+7°} _{-3°}	3° ^{+7°} _{-3°}

P20GR-65-225C-2

RECOMMENDED SOLDERING CONDITIONS

Solder this product under the following recommended conditions.

For details of the recommended soldering conditions, refer to information document **Semiconductor Device Mounting Technology Manual (C10535E)**.

Surface Mount Type

μPD16818GS 20-pin plastic SOP (300 mil)

μPD16818GR-8JG 20-pin plastic SSOP (225 mil)

Soldering Method	Soldering Conditions	Symbol of Recommended Soldering
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds MAX.(210°C MIN.), Number of times: 3 MAX., Number of days: None ^{Note} , Flux: Rosin-based flux with little chlorine component (chlorine: 0.2 Wt% MAX.)	IR35-00-3
VPS	Package peak temperature: 215°C, Time: 40 seconds MAX.(200°C MIN.), Number of times: 3 MAX., Number of days: None ^{Note} , Flux: Rosin-based flux with little chlorine component (chlorine: 0.2 Wt% MAX.)	VP15-00-3
Wave soldering	Package peak temperature: 260°C, Time: 10 seconds MAX., Preheating temperature: 120 °C MAX., Number of times: 1, Flux: Rosin-based flux with little chlorine component (chlorine: 0.2 Wt% MAX.)	WS60-00-1

Note Number of days in storage after the dry pack has been opened. The storage conditions are at 25 °C, 65 % RH MAX.

Caution Do not use two or more soldering methods in combination.

[MEMO]

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